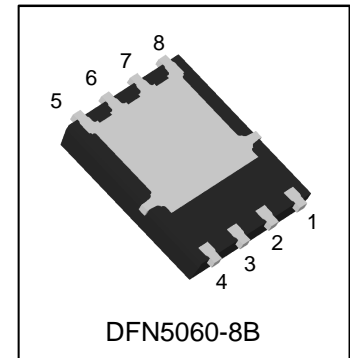


LP73035DT1WG

P-Channel 30-V (D-S) MOSFET

1. FEATURES

- Low RDS(on) trench technology.
- Low thermal impedance.
- Fast switching speed.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.

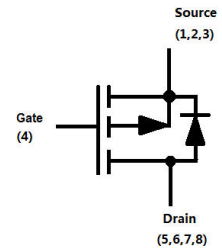


2. APPLICATIONS

- Load Switches.
- DC/DC Conversion.
- Motor Drives.

3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
LP73035DT1WG	LP73035	3000/Tape&Reel



4. MAXIMUM RATINGS(Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-to-Source Voltage		VDSS	-30	V
Gate-to-Source Voltage		VGS	± 20	V
Avalanche Current		IAS	55	A
Avalanche energy L=0.1mH		EAS	151.25	mJ
Continuous Drain Current(Note 1)	TA =25°C	ID	-30	A
	TA =70°C		-23	
	TC =25°C		-105	
	TC =70°C		-80	
Pulsed Drain Current (Note 2)		IDM	-120	
Power Dissipation(Note 1)	TA =25°C	PD	5	W
	TC =25°C		50	
Operating Junction Temperature		TJ	-55 ~+150	°C
Storage Temperature Range		Tstg	-55 ~+150	

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Max	Unit
Junction-to-Ambient(Note 1)	RθJA	50	°C/W
Junction-to-Case	RθJC	2.5	

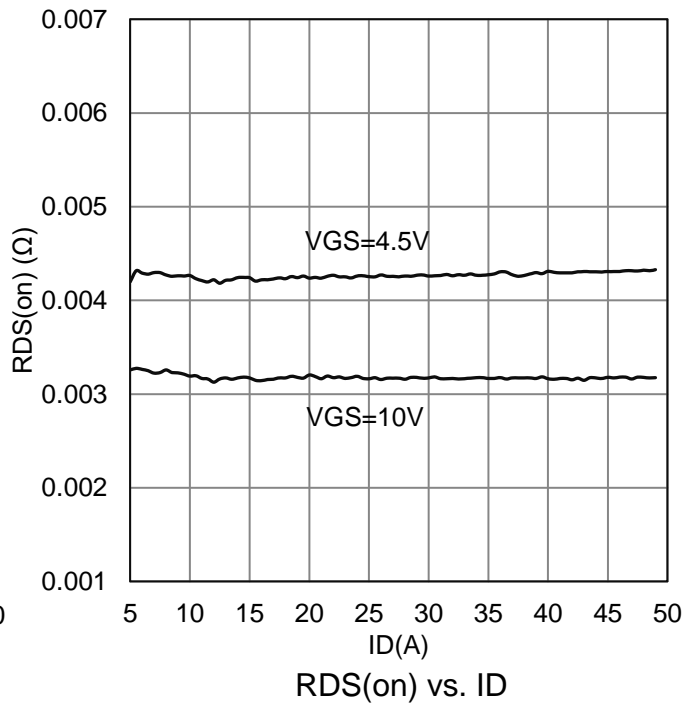
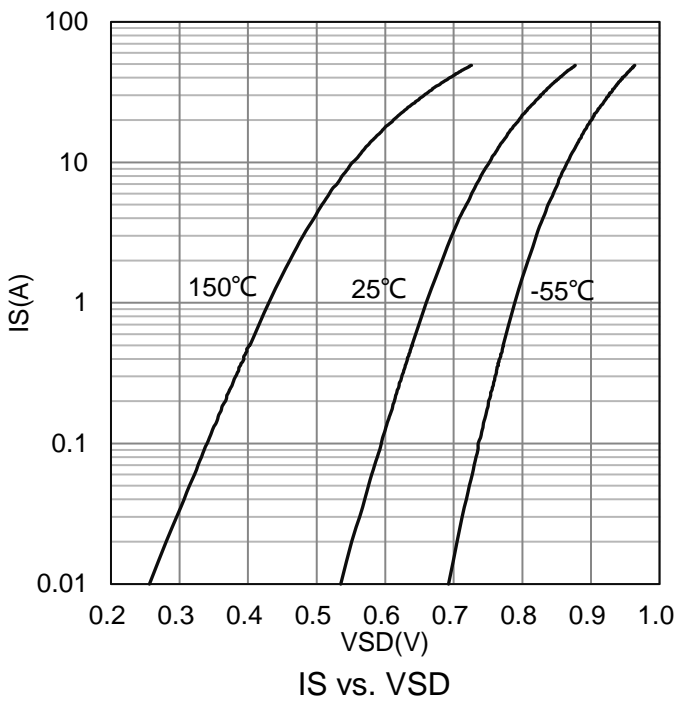
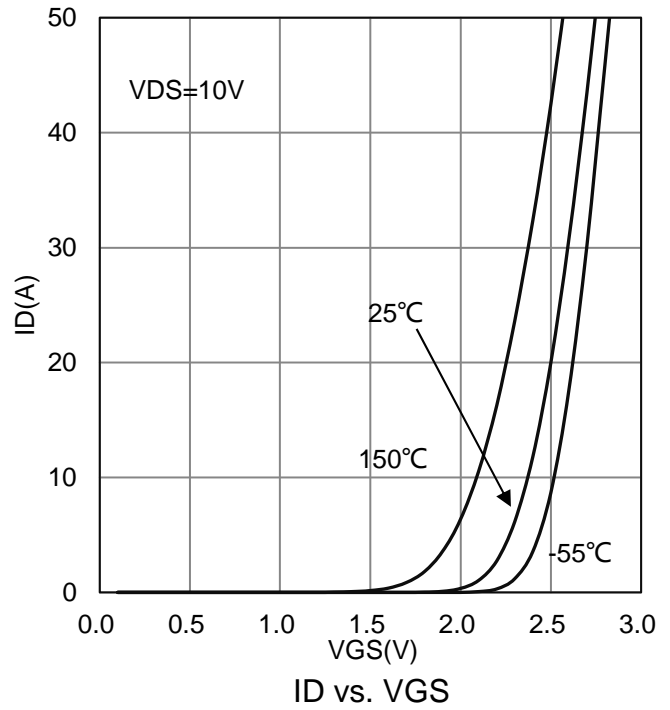
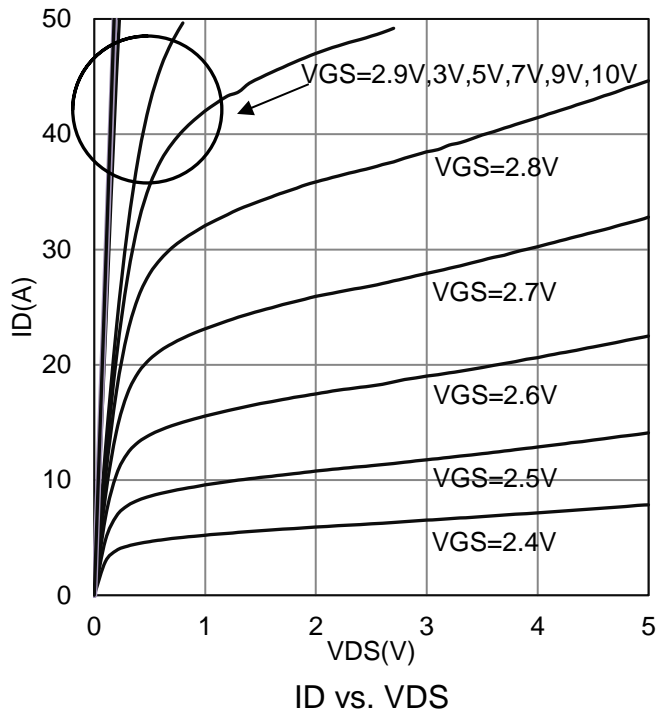
- 1.Surface mounted on "1.5 x 1.5" FR4 board using 1 sq in pad, 2 oz Cu.
- 2.Pulse width limited by maximum junction temperature

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

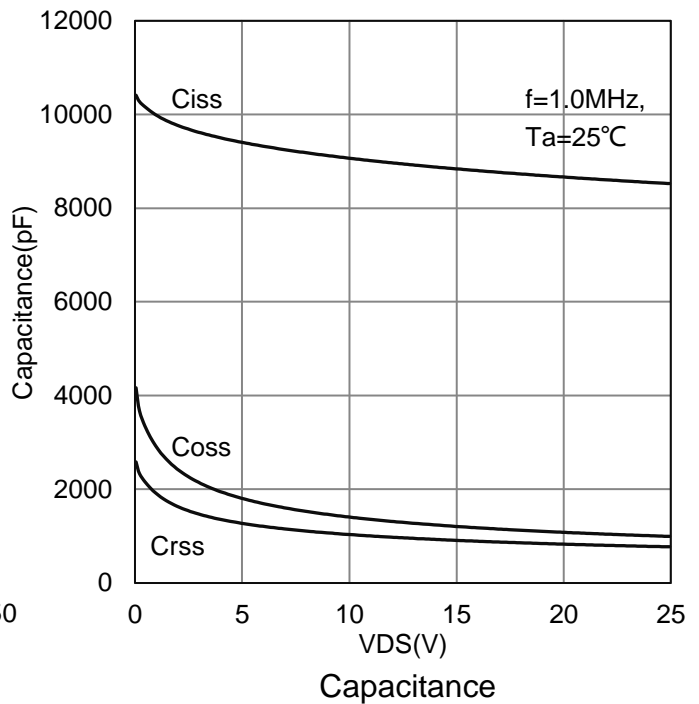
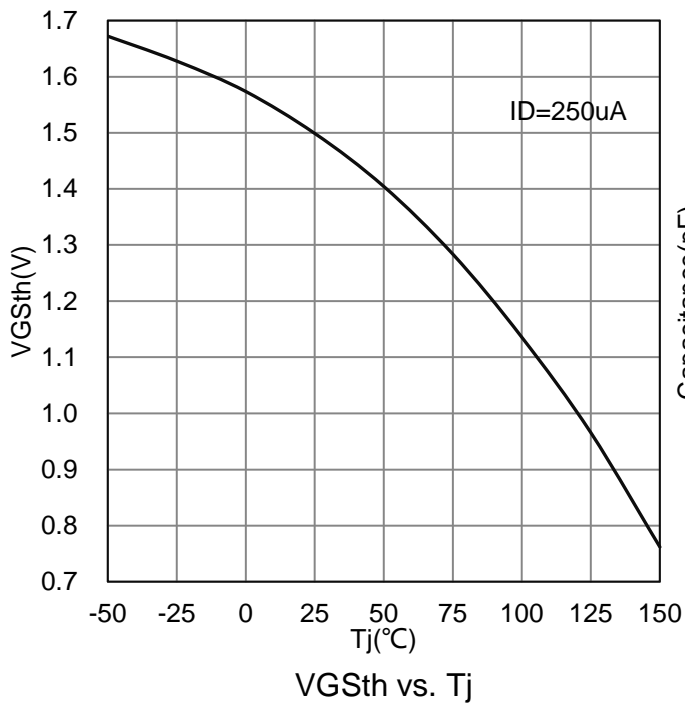
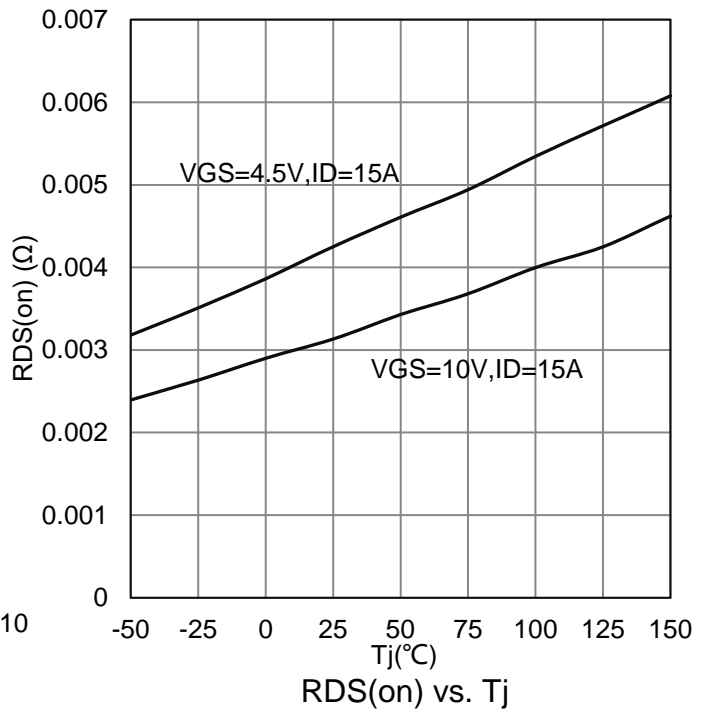
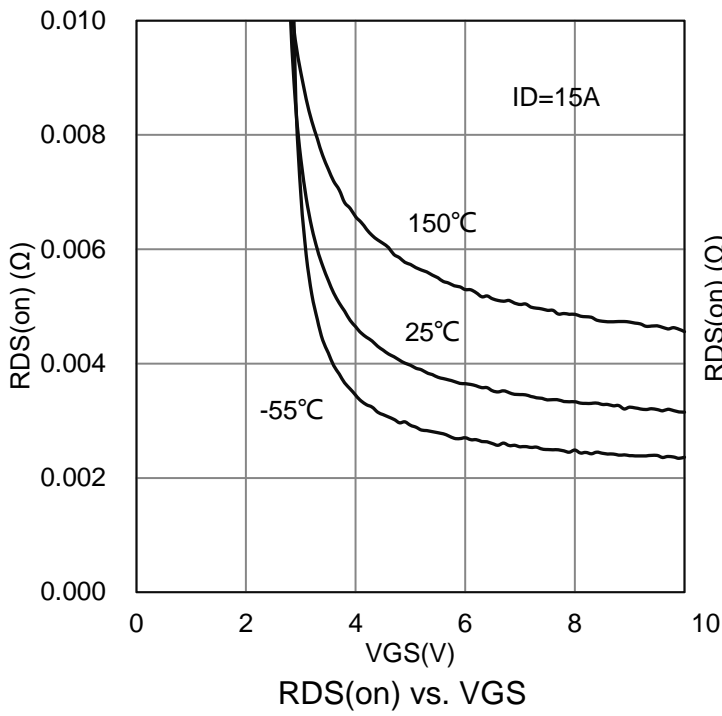
Characteristic	Symbol	Min.	Typ.	Max.	Unit
Static					
Drain-Source Breakdown Voltage (VGS=0 , ID = -250 μ A)	V(BR)DSS	-30	-	-	V
Gate-Source Threshold Voltage (VDS = VGS , ID = -250 μ A)	VGS(th)	-1	-	-2.5	V
Gate-Body Leakage (VDS = 0 V, VGS = \pm 20 V)	IGSS	-	-	\pm 100	nA
Zero Gate Voltage Drain Current (VDS = -30 V, VGS = 0 V)	IDSS	-	-	-1	μ A
Drain-Source On-Resistance(Note 3) (VGS = -10 V, ID = -15 A) (VGS = -4.5 V, ID = -15 A)	RDS(on)	-	-	3.7 5	m Ω
Diode Forward Voltage(Note 3) (IS = -2A, VGS = 0 V)	VSD	-	-	-1.2	V
Dynamic(Note 4)					
Total Gate Charge	(VDS = -24 V, VGS = -10 V, ID = -10 A)	Qg	-	166	nC
Gate-Source Charge		Qgs	-	21	
Gate-Drain Charge		Qgd	-	35	
Input Capacitance	(VDS = -25 V, VGS = 0 V, f = 1 MHz)	Ciss	-	8522	pF
Output Capacitance		Coss	-	993	
Reverse Transfer Capacitance		Crss	-	770	
Turn-On Delay Time	(VDS=-15 V, RL=1.5 Ω , ID=- 10A, VGEN=-10 V, RGEN=5 Ω)	td(on)	-	17	ns
Rise Time		tr	-	61	
Turn-Off Delay Time		td(off)	-	200	
Fall Time		tf	-	113	
Gate-Resistance (VDS=0V, VGS=0V, f=1.0MHz)	Rg	-	3.6	-	Ω

3. Pulse test: PW \leq 300 μ s duty cycle \leq 2%.

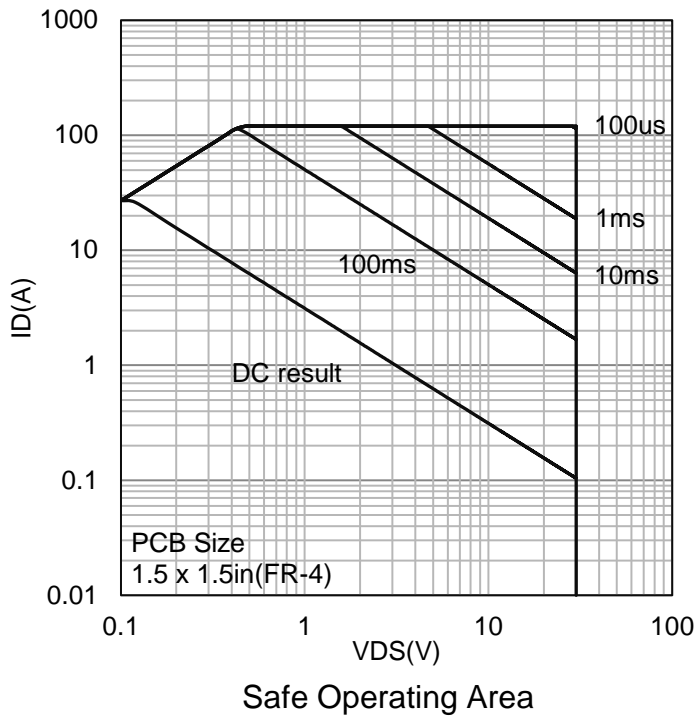
7. ELECTRICAL CHARACTERISTICS CURVES



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)

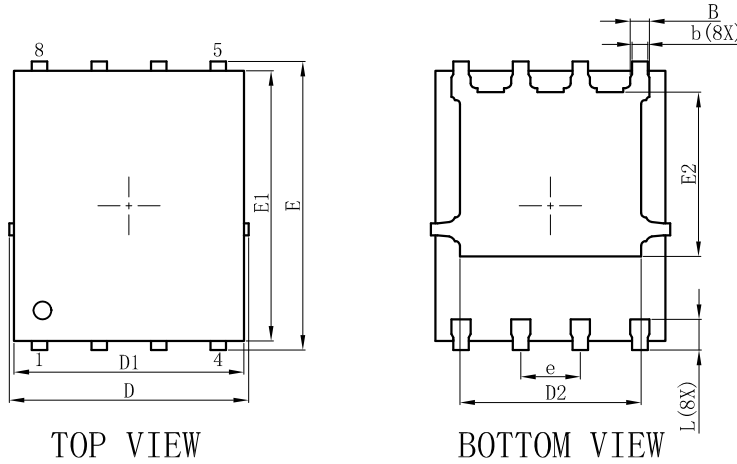


7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



7. OUTLINE AND DIMENSIONS

DFN5060-8B

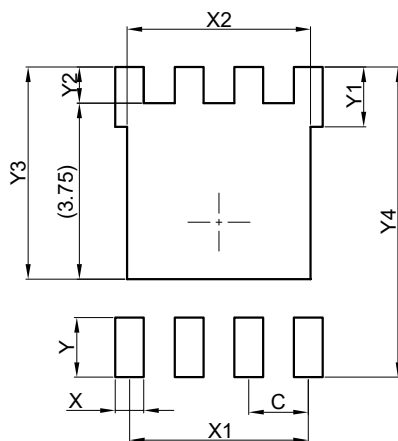


DFN5060-8B			
DIM	MIN	NOR	MAX
A	0.90	1.00	1.10
A1	0.00	0.02	0.05
E	6.00	6.15	6.30
E1	5.66	5.76	5.86
E2	3.40	3.50	3.60
D	4.95	5.10	5.25
D1	4.80	4.90	5.00
D2	3.76	3.86	3.96
b	0.30	0.35	0.40
B	0.36	0.41	0.46
L	0.56	0.66	0.76
e	1.27BSC		
c	0.254REF.		
θ	0°	-	12°
All Dimensions in mm			

GENERAL NOTES

1. Top package surface finish $Ra0.4 \pm 0.2\mu m$
2. Bottom package surface finish $Ra0.7 \pm 0.2\mu m$
3. Side package surface finish $Ra0.4 \pm 0.2\mu m$
4. Protrusion or Gate Burrs shall not exceed 0.05mm per side.
5. Offcenter Max0.038mm; Mismatch Max 0.038mm.

8. SOLDERING FOOTPRINT



DFN5060-8B	
DIM	(mm)
C	1.27
X	0.61
X1	3.81
X2	3.91
Y	1.27
Y1	1.27
Y2	0.77
Y3	4.52
Y4	6.61

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- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.

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